

NPN SILICON RF MICROWAVE TRANSISTOR

DESCRIPTION:

The **ASI MS2608** is Designed for pulsed S-Band radar applications from 2.7 to 3.1 GHz.

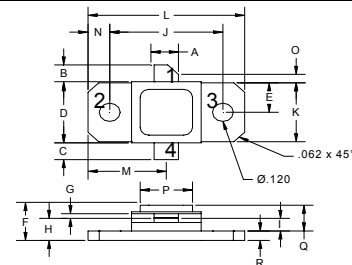
FEATURES:

- Internal Input/Output Matching Network
- $P_G = 6.0$ dB at 12 W/2.7-3.1 GHz
- *Omnigold*™ Metalization System

MAXIMUM RATINGS

I_C	2.0 A
V_{CC}	46 V
P_{DISS}	50 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	4.0 °C/W

PACKAGE STYLE .400 2L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.140 / 3.56	
B	.110 / 2.80	
C	.110 / 2.80	
D	.395 / 10.03	.407 / 10.34
E	.193 / 4.90	
F		.230 / 5.84
G	.003 / 0.08	.006 / 0.15
H	.118 / 3.00	.131 / 3.33
I	.063 / 1.60	
J	.650 / 16.51	
K	.386 / 9.80	
L	.900 / 22.86	
M	.450 / 11.43	
N	.125 / 3.18	
O	.050 / 1.27	
P	.405 / 10.29	
Q	.170 / 4.32	
R	.062 / 1.58	

1 = COLLECTOR 2&3 = BASE 4 = EMITTER

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 7.0$ mA	55			V
BV_{CER}	$I_C = 7.0$ mA $R_{BE} = 10$ Ω	55			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CES}	$V_{CE} = 40$ V			5.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 600$ mA	30		150	---
P_G	$V_{CC} = 40$ V $P_{OUT} = 12$ W $f = 2.7$ to 3.1 GHz	6.0			dB
η_C		30			%

Note:

Pulse Widht = 100 μS

Duty Cycle = 10 %